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## W-112

## B. Tech. (Weekend) EXAMINATION, Dec. 2017

(First Semester)

(Re-appear Only)

## ELECTRICAL ENGINEERING MATERIALS AND SEMICONDUCTOR DEVICES

ECE(W)-101

(Common for All Branches)

Time: 3 Hours [Maximum Marks: 100]

Before answering the question-paper candidates should ensure that they have been supplied to correct and complete question-paper. No complaint, in this regard, will be entertained after the examination.

**Note**: Attempt any *Five* questions. All questions carry equal marks.

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P.T.O.

1.	(a)	Define the terms relaxation time collision time. Also, discuss the type		6.	(a)	Differentiate between UJT and BJT. 10
		thermal conductivity and effect magnetic field.			(b)	Briefly explain the construction, working and applications of MOSFET. 10
	(b)	Explain the role and importance superconductivity and energy bands.		7.		efly describe the construction and operation he following using suitable schematics:
2.	(a)	Briefly discuss types of dielectric insulating materials.	and <b>10</b>		(i) (ii)	Diac GTO. <b>10+10</b>
	(b)	What do you understand by the to	erms		(11)	G10.
		dielectric loss, electrostriction and	loss	8.	Wri	te short notes on the following:
		tangent? Also discuss the mechanism			(i)	IGBT
		polarization.	10		(ii)	Planar technology for device fabrication.
3.	(a)	Differentiate between magnetic morand dipole moment.	ment 10			10+10
	(b)	Discuss in detail eddy current	and			
		hysteresis losses.	10			
4.	What do you understand by diffusion and transition capacitance of P-N junction? Briefly explain the operation of P-N junction. 20					
5.	5. Describe the construction and working of the					
	follo	owing:	10			
	(i)	LED				
	(ii)	Solar-Cell.				

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